

MOSFETs Silicon N-Channel MOS

SSM3K337R

1. Applications

· Relay Drivers

2. Features

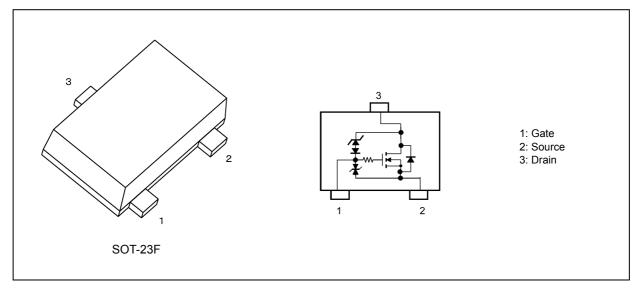
- (1) AEC-Q101 Qualified (Note1).
- (2) 4.0-V gate drive voltage.
- (3) Low drain-source on-resistance
 - : $R_{DS(ON)} = 200 \text{ m}\Omega \text{ (max) (@V_{GS} = 4.0 V, I_D = 1.0 A)}$

 $R_{DS(ON)} = 176 \text{ m}\Omega \text{ (max) (@V_{GS} = 4.5 V, I_D = 2.0 A)}$

 $R_{DS(ON)}$ = 150 m Ω (max) (@ V_{GS} = 10 V, I_D = 2.0 A)

Note 1: For detail information, please contact to our sales.

3. Packaging and Pin Assignment





4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V _{DS(DC)}	38	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)		(Note 1)	I _D	2	Α
Drain current (pulsed)		(Note 1), (Note 2)	I _{DP}	6	
Power dissipation		(Note 3)	P_D	1	W
Power dissipation	(t ≤ 10 s)	(Note 3)	P _D	2	
Channel temperature			T _{ch}	150	°C
Single-pulse active clamp capability		(Note 4)	E _{AS}	4.5	mJ
Storage temperature			T _{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW) \leq 10 ms, duty \leq 1%
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm²)
- Note 4: V_{DD} = 25 V, T_{ch} = 25°C (Initial state), L = 1 mH

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-off current		I _{DSS}	V _{DS} = 30.4 V, V _{GS} = 0 V	_	_	10	
Drain-source clamp voltage		V _{(CL)DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	38	43	48	V
Gate threshold voltage	(Note 1)	V_{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	0.7	_	1.7	V
Drain-source on-resistance	(Note 2)	R _{DS(ON)}	I _D = 2.0 A, V _{GS} = 10 V	_	135	150	mΩ
			I _D = 2.0 A, V _{GS} = 4.5 V	_	155	176	
			I _D = 1.0 A, V _{GS} = 4.0 V	_	161	200	
Forward transfer admittance	(Note 2)	Y _{fs}	V _{DS} = 10 V, I _D = 1.0 A	_	4.1	_	S

Note 1: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{\text{GS(ON)}}$ must be higher than V_{th} , and $V_{\text{GS(OFF)}}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$. Take this into consideration when using the device.

Note 2: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	_	120		pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz		7.2		
Output capacitance	Coss		_	33		
Switching time (turn-on time)	t _{on}	$V_{DD} = 20 \text{ V}, I_D = 0.5 \text{ A}$	_	380		ns
Switching time (turn-off time)	t _{off}	V_{GS} = 0 to 4.5 V, R_{G} = 10 Ω See Chapter 5.3.		700	1	

5.3. Switching Time Test Circuit

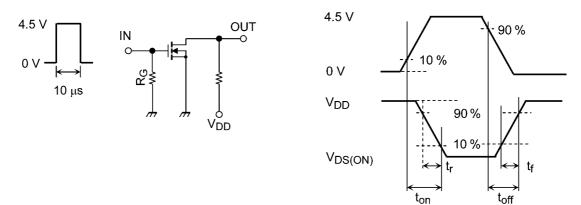


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V_{DD} = 30.4 V, V_{GS} = 10 V,	_	3.0		nC
Gate-source charge 1	Q _{gs1}	I _D = 1.0 A	_	0.6	_	
Gate-drain charge	Q_{gd}			0.5		



5.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	$I_D = -2.0 \text{ A}, V_{GS} = 0 \text{ V}$	_	-0.87	-1.2	V

Note 1: Pulse measurement.

6. Marking

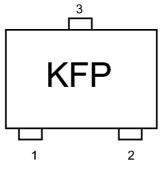


Fig. 6.1 Marking



7. Characteristics Curves (Note)

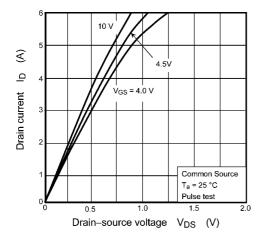


Fig. 7.1 I_D - V_{DS}

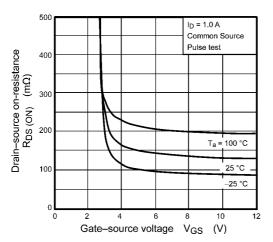


Fig. 7.3 R_{DS(ON)} - V_{GS}

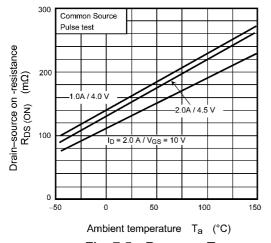


Fig. 7.5 R_{DS(ON)} - T_a

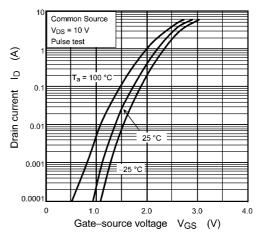


Fig. 7.2 $I_D - V_{GS}$

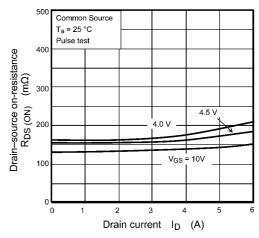


Fig. 7.4 R_{DS(ON)} - I_D

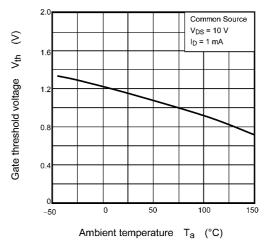


Fig. 7.6 V_{th} - T_a



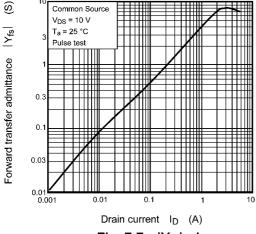
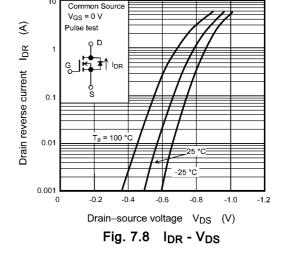


Fig. 7.7 $|Y_{fs}|$ - I_D



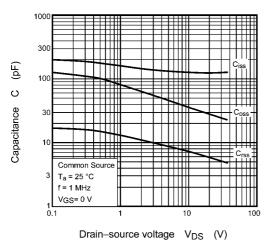


Fig. 7.9 C - V_{DS}

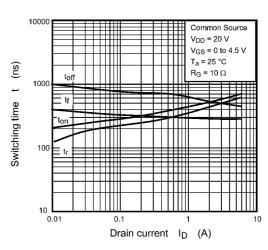


Fig. 7.10 t - I_D

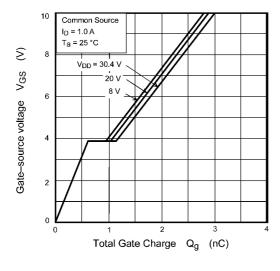


Fig. 7.11 Dynamic Input Characteristics

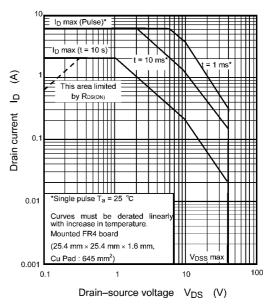
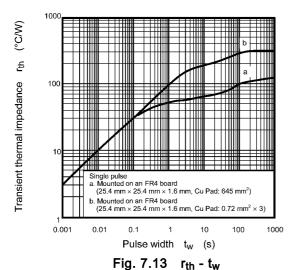
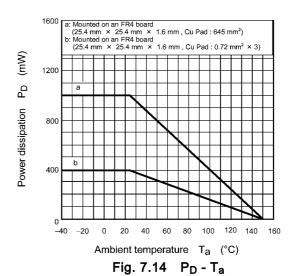


Fig. 7.12 Safe Operating Area

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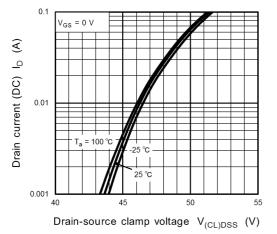


Fig. 7.15 I_D - V_{(CL)DSS}

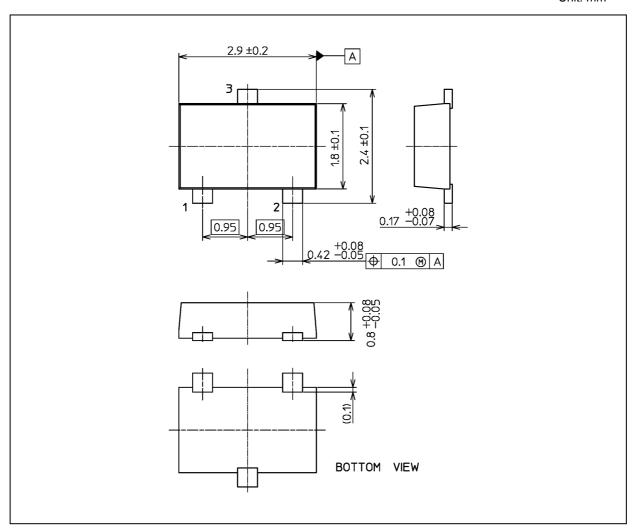
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	

Rev.6.0



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